V23990-P589-A31-PM

preliminary datasheet

flowPIM 1 3rd gen | **1200V / 25A**

Features

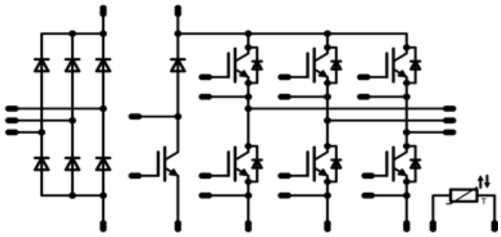
- 3~ rectifier, BRC, Inverter, NTC
- Very compact housing, easy to route
- IGBT2 phantom speed / EmCon4 technology
- Lower losses than IGBT3 or 4 for f_{sw} > 8kHz

flowPIM1 housing

Target Applications

- Motor Drives with 8kHz < f_{sw} < 30kHz
- Low audible noise applications (f_{sw} > 16kHz)
- High efficiency applications
- Centered aircon, fans, pumps

Schematic



Types

- V23990-P589-A31-PM

Maximum Ratings

Tj=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Input Rectifier Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
DC forward current	I_{FAV}	T_j=$T_j$max	T_h=80°C	36	A
Surge forward current	I_{FSM}	t_p=10ms	T_j=45°C	320	A
I^2t-value	I^2t			510	A^2s
Power dissipation per diode	P_{tot}	T_j=$T_j$max	T_h=80°C	40	W
Maximum junction temperature	$T_j$max			150	°C
Inverter Transistor					
Collector-emitter break down voltage	V_{CE}			1200	V
DC collector current	I_C	T_j=$T_j$max	T_h=80°C	27	A
Repetitive peak collector current	I_{Cpulse}	t_p limited by $T_j$max		75	A
Power dissipation per IGBT	P_{tot}	T_j=$T_j$max	T_h=80°C	67	W
Gate-emitter peak voltage	V_{GE}			±20	V
Maximum junction temperature	$T_j$max			150	°C

Maximum Ratings

Tj=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Inverter Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
DC forward current	I_F	$T_j=T_j$max	T_h=80°C	21	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max		50	A
Power dissipation per diode	P_{tot}	$T_j=T_j$max	T_h=80°C	37	W
Maximum junction temperature	$T_j$max			175	°C
Brc Transistor					
Collector-emitter break down voltage	V_{CE}			1200	V
DC collector current	I_C	$T_j=T_j$max	T_h=80°C	15	A
Repetitive peak collector current	I_{Cpuls}	t_p limited by $T_j$max		45	A
Power dissipation per IGBT	P_{tot}	$T_j=T_j$max	T_h=80°C	39	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150°C V_{GE}=15V		10 800	μs V
Maximum junction temperature	$T_j$max			175	°C
Brc Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
DC forward current	I_F	$T_j=T_j$max	T_h=80°C	10	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max		20	A
Power dissipation per diode	P_{tot}	$T_j=T_j$max	T_h=80°C	21	W
Maximum junction temperature	$T_j$max			175	°C
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{op}			-40…+(Tjmax - 25)	°C
Insulation Properties					
Insulation voltage	V_{is}	t=2s	DC voltage	4000	V
Creepage distance				min 12.7	mm
Clearance				min 12.7	mm

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Input Rectifier Diode										
Forward voltage	V_F				50	Tj=25°C Tj=125°C	0.8	1.29 1.24	1.6	V
Threshold voltage (for power loss calc. only)	V_{to}				50	Tj=25°C Tj=125°C		0.93 0.82		V
Slope resistance (for power loss calc. only)	r_t				50	Tj=25°C Tj=125°C		7 9		mΩ
Reverse current	I_r			1600		Tj=25°C Tj=150°C			0.02 2	mA
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50μm λ=0.61W/mK						1.77		K/W
Thermal resistance chip to case per chip	R_{thJC}							N/A		
Inverter Transistor										
Gate emitter threshold voltage	$V_{GE(th)}$	VCE=VGE			0.001	Tj=25°C Tj=125°C	4.5	5.5	6.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		25	Tj=25°C Tj=125°C	1.5	2.13 2.32	2.75	V
Collector-emitter cut-off current incl. diode	I_{CES}		0	1200		Tj=25°C Tj=125°C			0.01	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25°C Tj=125°C			200	nA
Integrated gate resistor	R_{gint}							-		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=16Ω Rgon=16Ω	±15	600	25	Tj=25°C Tj=125°C		136 137		ns
Rise time	t_r					Tj=25°C Tj=125°C		13.2 15.8		
Turn-off delay time	$t_{d(off)}$					Tj=25°C Tj=125°C		201 235		
Fall time	t_f					Tj=25°C Tj=125°C		58 99		
Turn-on energy loss per pulse	E_{on}					Tj=25°C Tj=125°C		0.94 1.32		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25°C Tj=125°C		1.17 1.74		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25°C		2020		pF
Output capacitance	C_{oss}							193		
Reverse transfer capacitance	C_{rss}							64		
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50μm λ=0.61W/mK						1.05		K/W
Thermal resistance chip to case per chip	R_{thJC}							N/A		
Inverter Diode										
Diode forward voltage	V_F				25	Tj=25°C Tj=150°C	1.3	1.9 1.89	2.2	V
Peak reverse recovery current	I_{RRM}	Rgoff=16Ω	±15	600	25	Tj=25°C Tj=125°C		60 65		A
Reverse recovery time	t_{rr}					Tj=25°C Tj=125°C		84 153		ns
Reverse recovered charge	Q_{rr}					Tj=25°C Tj=125°C		2.68 4.64		μC
Peak rate of fall of recovery current	di(rec)max/dt					Tj=25°C Tj=125°C		4514 2719		A/μs
Reverse recovered energy	Erec					Tj=25°C Tj=125°C		1.25 2.14		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50μm λ=0.61W/mK						1.92		K/W
Thermal resistance chip to case per chip	R_{thJC}							N/A		

Characteristic Values

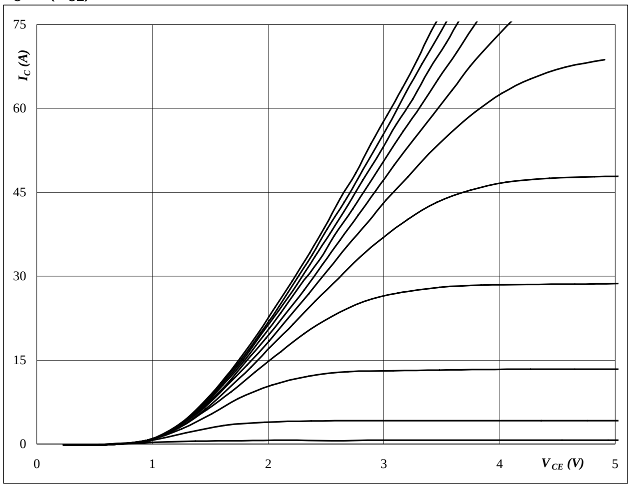
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Brc Transistor										
Gate emitter threshold voltage	$V_{GE(th)}$	VCE=VGE			0.0005	Tj=25°C Tj=150°C	5	5.8	6.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		15	Tj=25°C Tj=150°C	1.6	1.88 2.30	2.2	V
Collector-emitter cut-off incl. diode	I_{CES}		0	1200		Tj=25°C Tj=150°C			0.005	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25°C Tj=150°C			200	nA
Integrated gate resistor	R_{gint}							-		Ω
Turn-on delay time	$t_{d(on)}$	Rgon=32Ω Rgoff=32Ω	±15	600	15	Tj=25°C Tj=125°C		87 87		ns
Rise time	t_r					Tj=25°C Tj=125°C		24 28		
Turn-off delay time	$t_{d(off)}$					Tj=25°C Tj=125°C		194 256		
Fall time	t_f					Tj=25°C Tj=125°C		77 102		
Turn-on energy loss per pulse	E_{on}					Tj=25°C Tj=125°C		0.95 1.29		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25°C Tj=125°C		0.82 1.17		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25°C		900		pF
Output capacitance	C_{oss}							80		
Reverse transfer capacitance	C_{rss}							55		
Gate charge	Q_{Gate}	Vcc=960V	±15		15	Tj=25°C		120		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50µm λ=0.61W/mK						1.8		K/W
Thermal resistance chip to case per chip	R_{thJC}							N/A		
Brc Diode										
Diode forward voltage	V_F				10	Tj=25°C Tj=150°C	1.3	1.85 1.76	2.2	V
Reverse leakage current	I_r		±15	600	10	Tj=25°C Tj=150°C			5	µA
Peak reverse recovery current	I_{RRM}	Rgon=32Ω	±15	600	10	Tj=25°C Tj=125°C		10 12		A
Reverse recovery time	t_{rr}					Tj=25°C Tj=125°C		324 489		ns
Reverse recovered charge	Q_{rr}					Tj=25°C Tj=125°C		1.38 2.27		µC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25°C Tj=125°C		46 46		A/µs
Reverse recovery energy	E_{rec}					Tj=25°C Tj=125°C		0.58 0.96		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50µm λ=0.61W/mK						3.28		K/W
Thermal resistance chip to case per chip	R_{thJC}							N/A		
Thermistor										
Rated resistance	R					Tj=25°C Tj=125°C	20.9	22 0.75	23.1	kΩ
Operating current	I					Tj=25°C			0.3	mA
Power dissipation	P					Tj=25°C		200		mW
B-value	$B_{(25/50)}$	Tol. ±3%				Tj=25°C		3950		K

Output Inverter

Figure 1 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



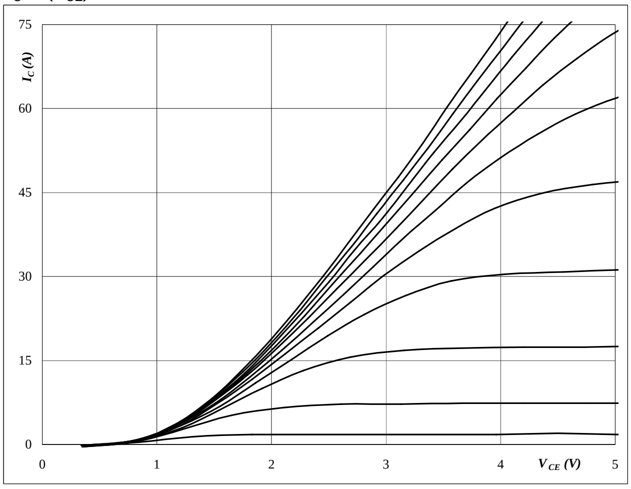
At

t_p =	250	µs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 2 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



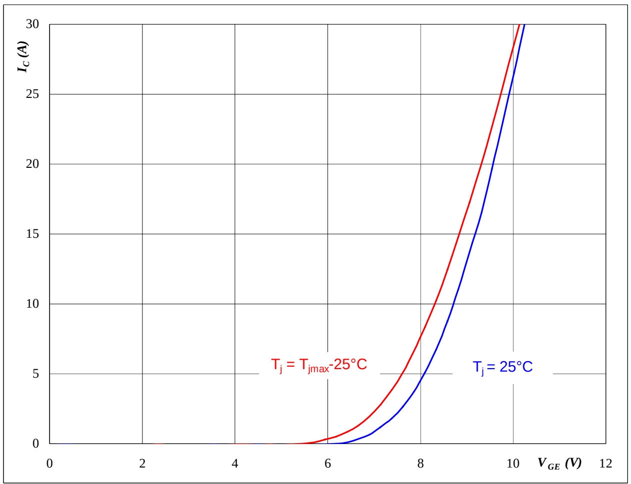
At

t_p =	250	µs
T_j =	125	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 3 Output inverter IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



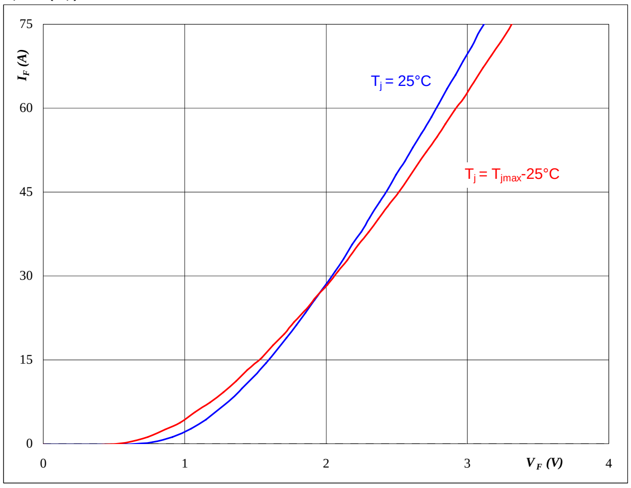
At

t_p =	250	µs
V_{CE} =	10	V

Figure 4 Output inverter FRED

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

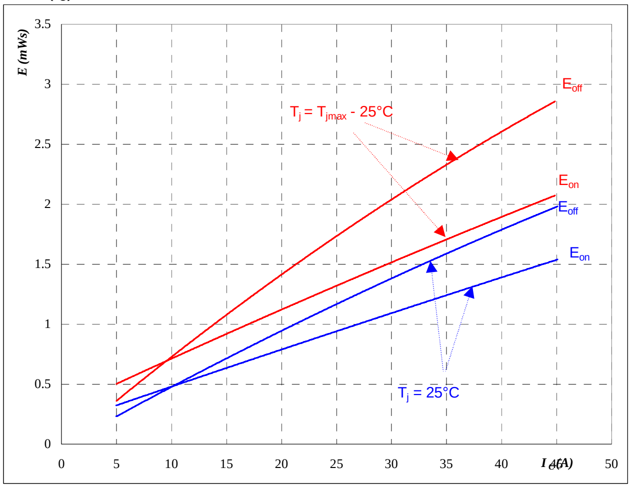
t_p =	250	µs

Output Inverter

Figure 5 Output inverter IGBT

Typical switching energy losses as a function of collector current

E = f(I_C)



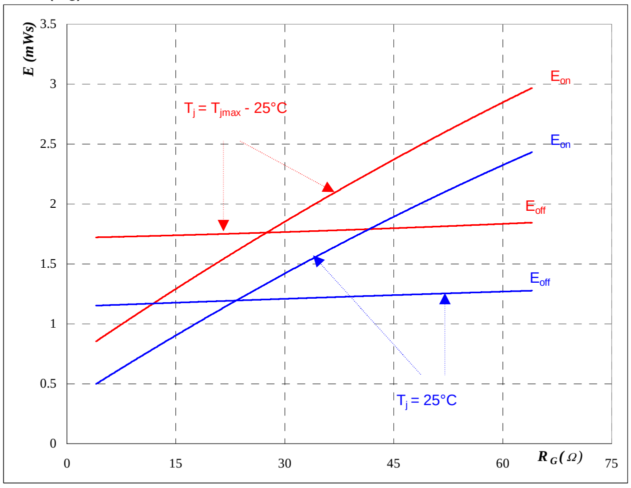
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

Figure 6 Output inverter IGBT

Typical switching energy losses as a function of gate resistor

E = f(R_G)



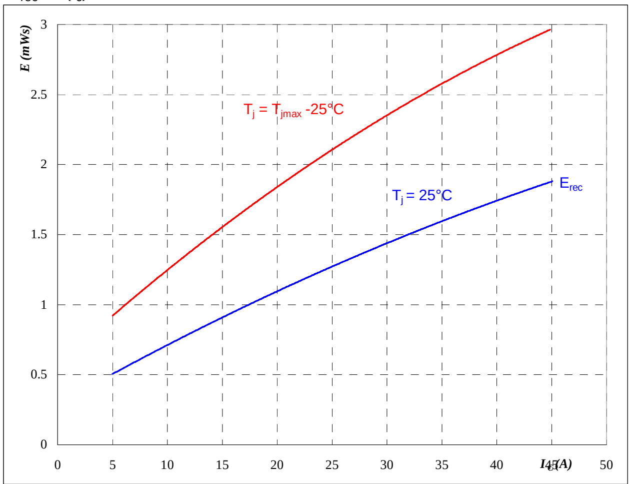
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

Figure 7 Output inverter IGBT

Typical reverse recovery energy loss as a function of collector current

E_{rec} = f(I_c)



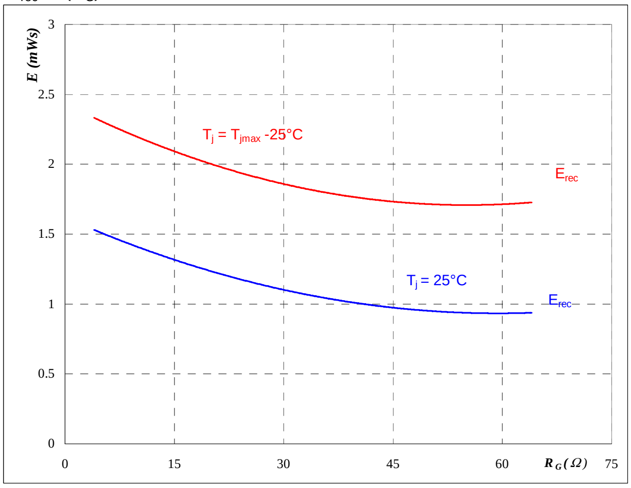
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

Figure 8 Output inverter IGBT

Typical reverse recovery energy loss as a function of gate resistor

E_{rec} = f(R_G)



With an inductive load at

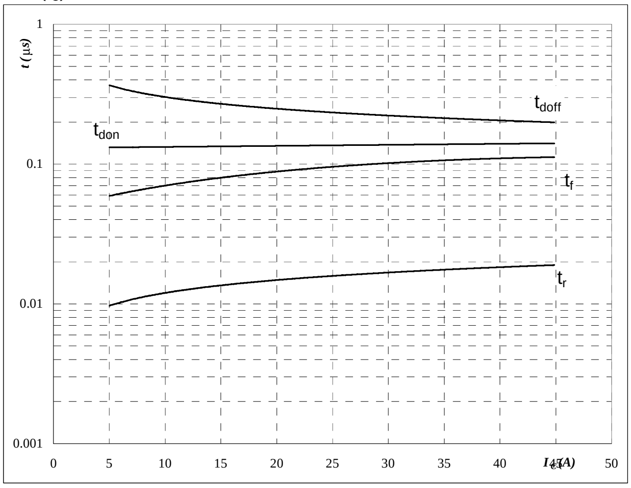
T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

Output Inverter

Figure 9 Output inverter IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



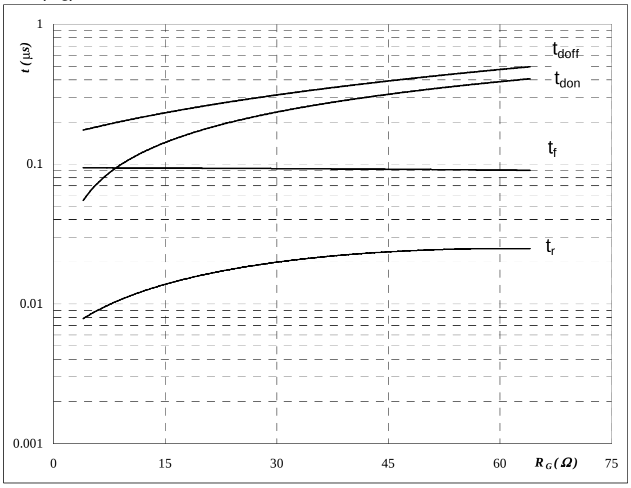
With an inductive load at

T_j =	125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

Figure 10 Output inverter IGBT

Typical switching times as a function of gate resistor

$t = f(R_G)$



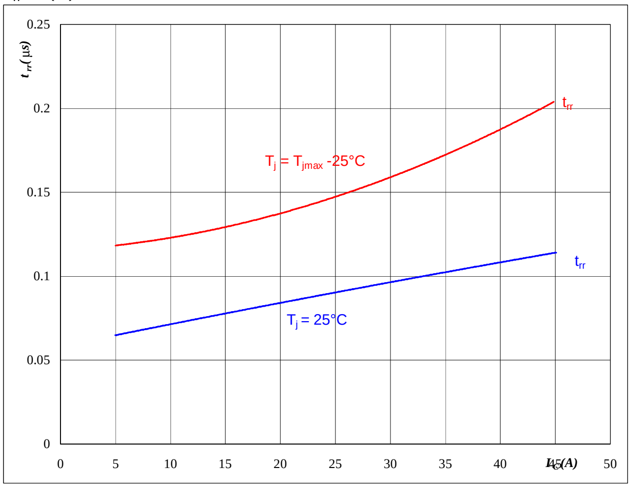
With an inductive load at

T_j =	125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	25	A

Figure 11 Output inverter FRED

Typical reverse recovery time as a function of collector current

$t_{rr} = f(Ic)$



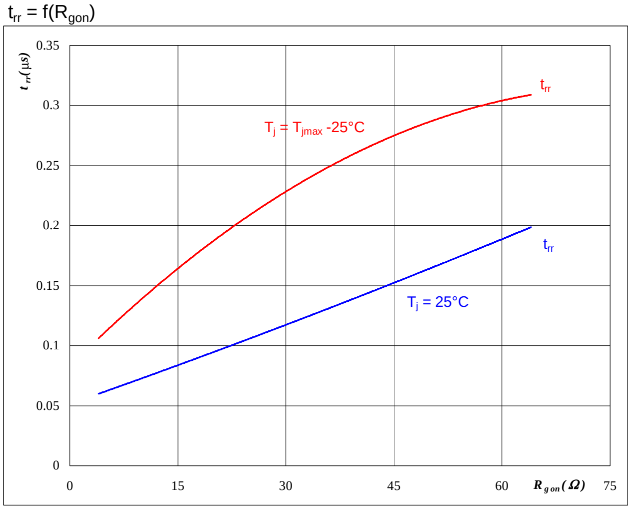
At

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

Figure 12 Output inverter FRED

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



At

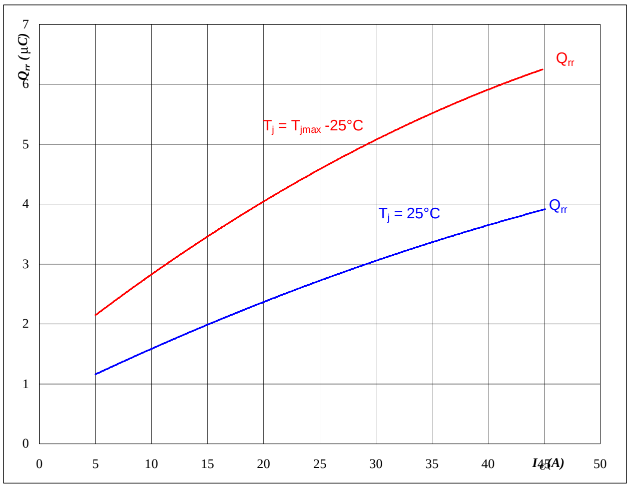
T_j =	25/125	°C
V_R =	600	V
I_F =	25	A
V_{GE} =	±15	V

Output Inverter

Figure 13	Output inverter FRED

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



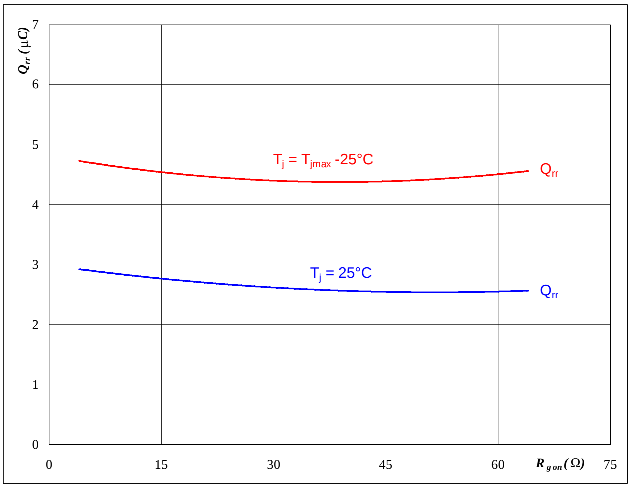
At

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

Figure 14	Output inverter FRED

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



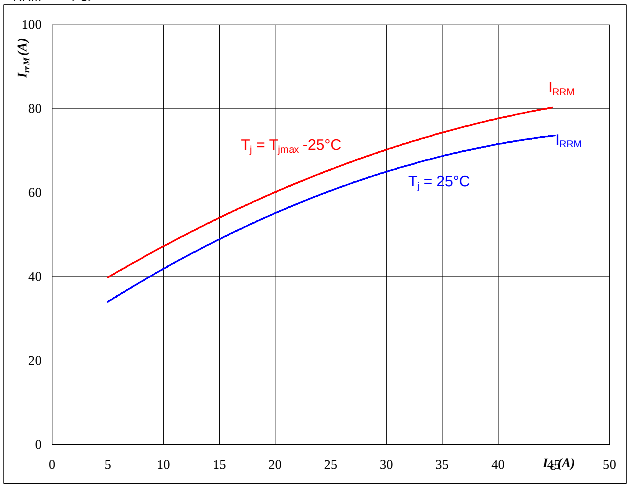
At

T_j =	25/125	°C
V_R =	600	V
I_F =	25	A
V_{GE} =	±15	V

Figure 15	Output inverter FRED

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



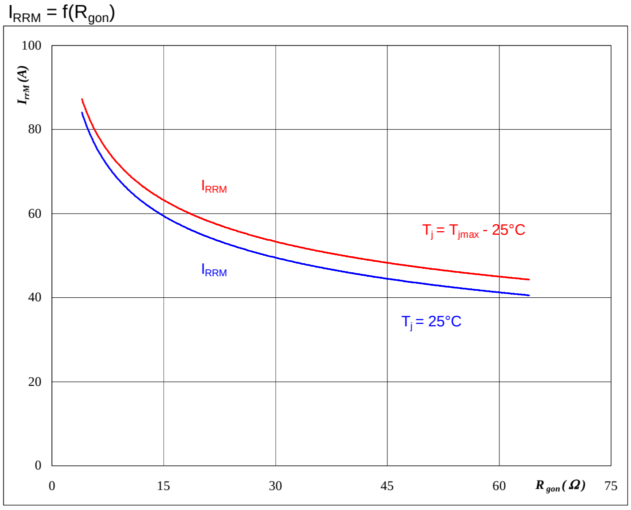
At

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

Figure 16	Output inverter FRED

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

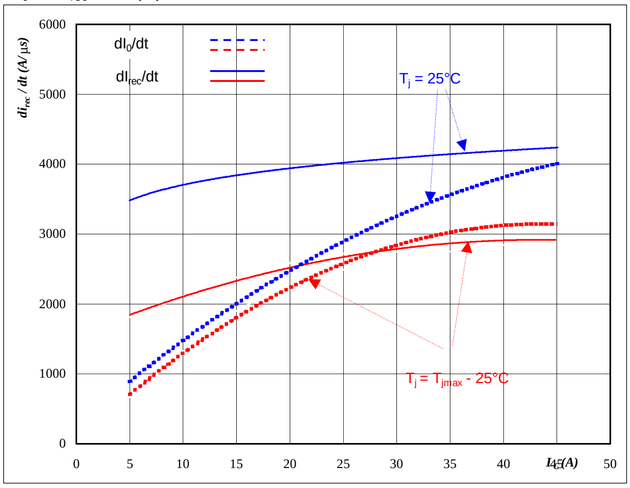
T_j =	25/125	°C
V_R =	600	V
I_F =	25	A
V_{GE} =	±15	V

Output Inverter

Figure 17 Output inverter FRED

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(Ic)$



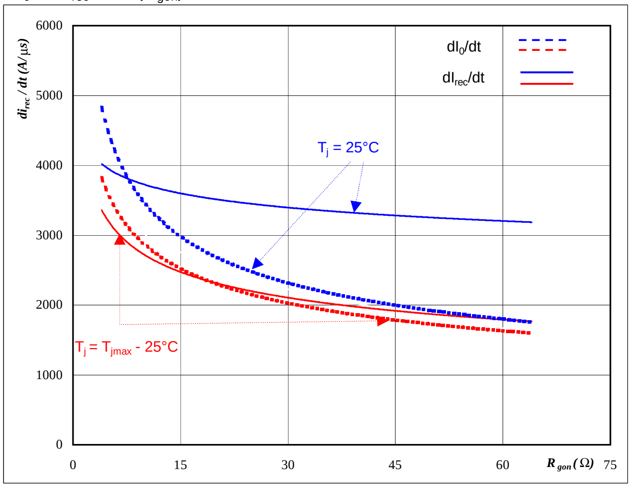
At

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	16	Ω

Figure 18 Output inverter FRED

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



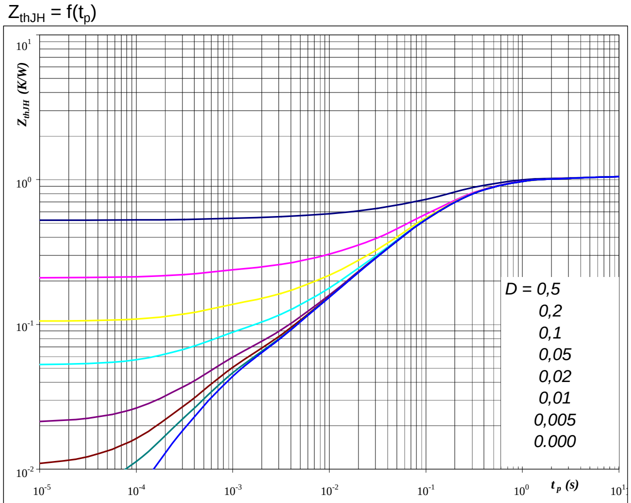
At

T_j =	25/125	°C
V_R =	600	V
I_F =	25	A
V_{GE} =	±15	V

Figure 19 Output inverter IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T				
R_{thJH} =	1.05	K/W	RthJH =	1.05	K/W
Single device heated			All devices heated		

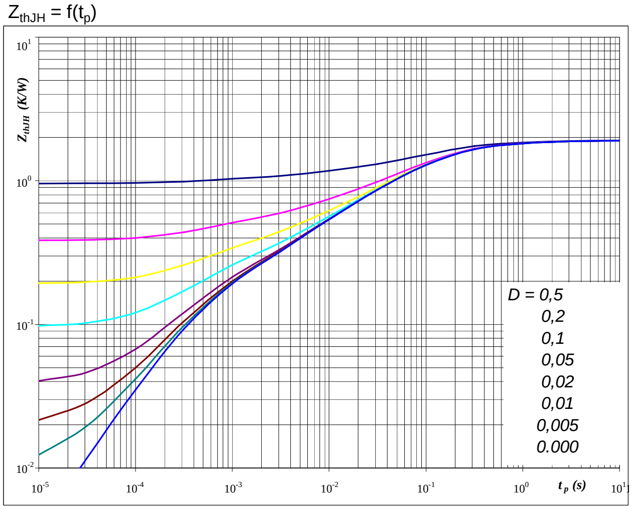
IGBT thermal model values

R (C/W)	Tau (s)	R (C/W)
0.09	2.6E+00	0.09
0.42	3.2E-01	0.42
0.41	8.5E-02	0.41
0.09	1.0E-02	0.09
0.04	6.4E-04	0.04

Figure 20 Output inverter FRED

FRED transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

D =	t_p / T				
R_{thJH} =	1.92	K/W	RthJH =	1.92	K/W
Single device heated			All devices heated		

FRED thermal model values

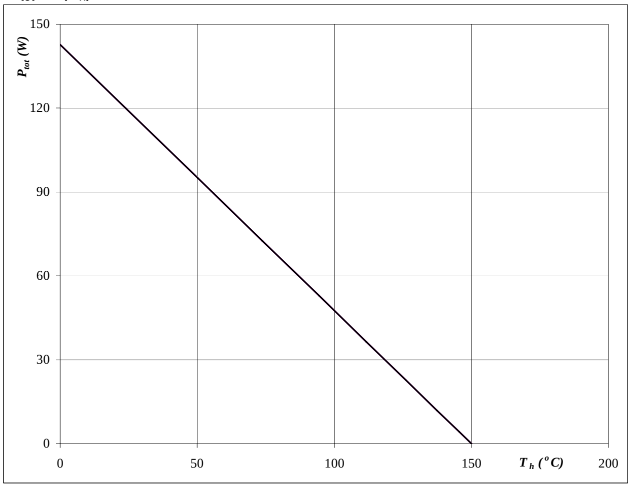
R (C/W)	Tau (s)	R (C/W)
0.04	9.5E+00	0.04
0.21	7.9E-01	0.21
0.80	1.3E-01	0.80
0.51	2.8E-02	0.51
0.21	4.1E-03	0.21
0.14	4.5E-04	0.14

Output Inverter

Figure 21 Output inverter IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



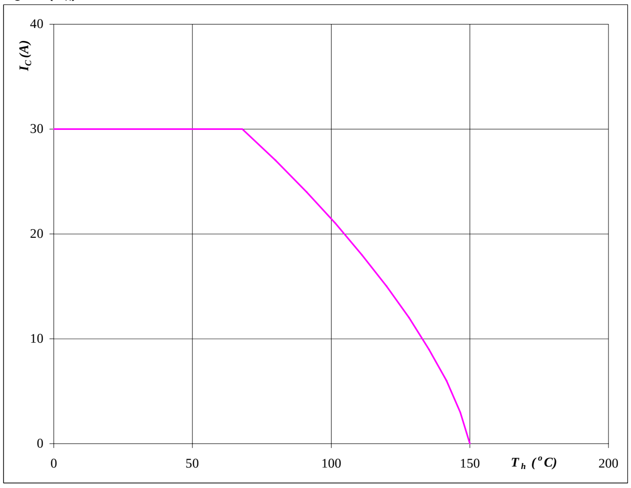
At
T_j = 150 °C

single heating
overall heating

Figure 22 Output inverter IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$

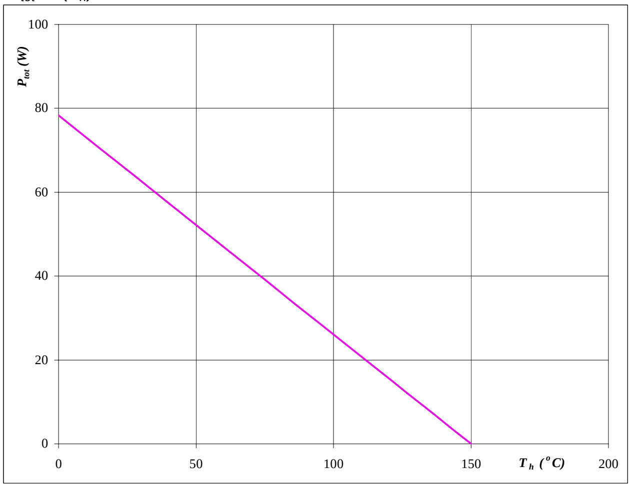


At
T_j = 150 °C
V_{GE} = 15 V

Figure 23 Output inverter FRED

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



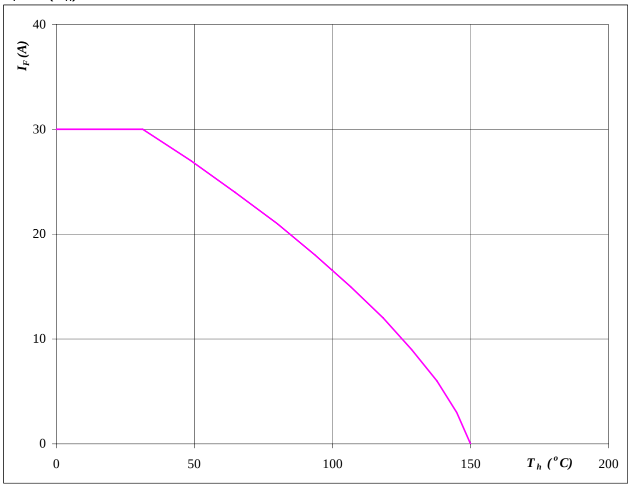
At
T_j = 150 °C

single heating
overall heating

Figure 24 Output inverter FRED

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



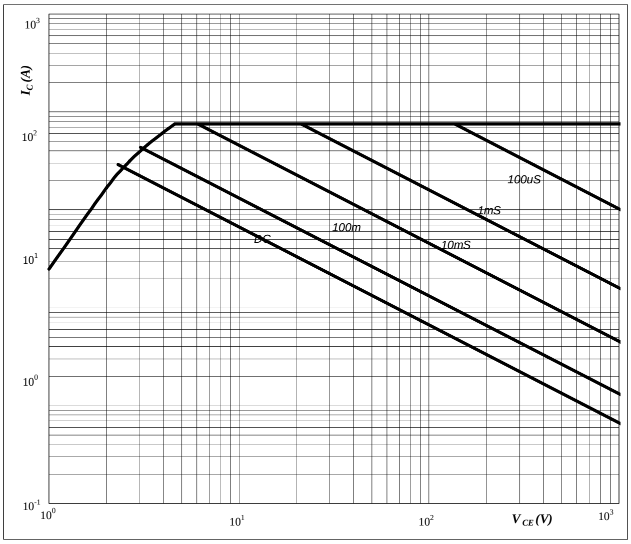
At
T_j = 150 °C

Output Inverter

Figure 25 Output inverter IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



At

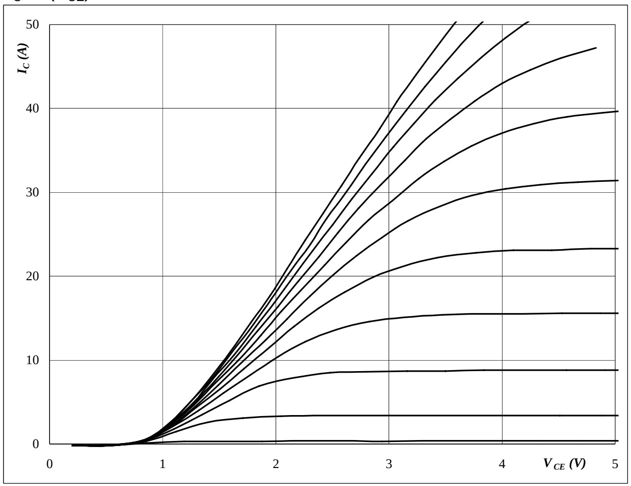
D =	single pulse	
Th =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	ºC

Brake

Figure 1 Brake IGBT

Typical output characteristics

$I_C = f(V_{CE})$



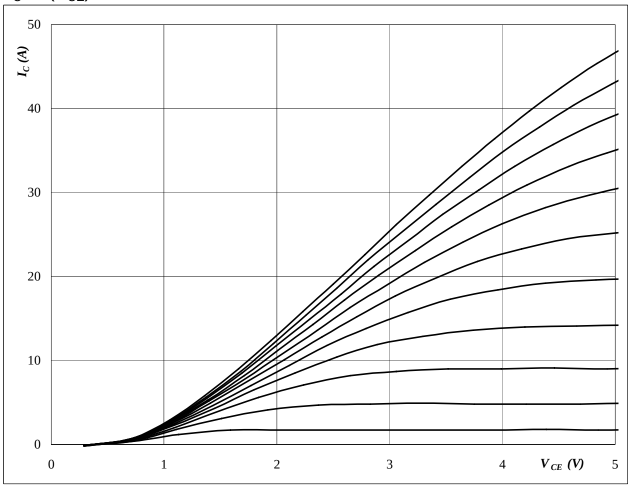
At

t_p =	250	µs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 2 Brake IGBT

Typical output characteristics

$I_C = f(V_{CE})$



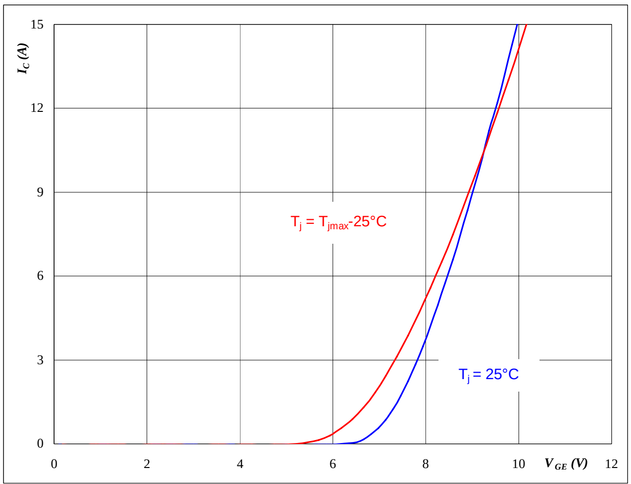
At

t_p =	250	µs
T_j =	125	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

Figure 3 Brake IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



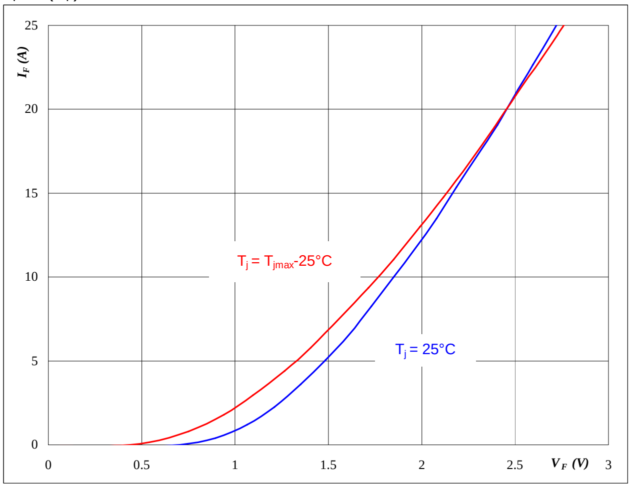
At

t_p =	250	µs
V_{CE} =	10	V

Figure 4 Brake FRED

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

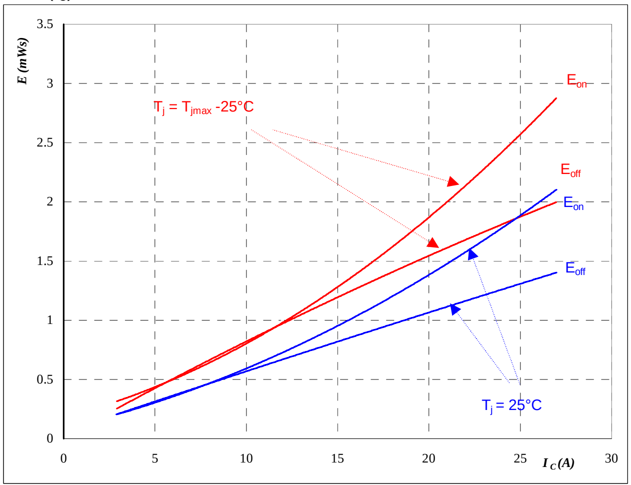
t_p =	250	µs

Brake

Figure 5 — Brake IGBT

Typical switching energy losses as a function of collector current

$E = f(I_C)$



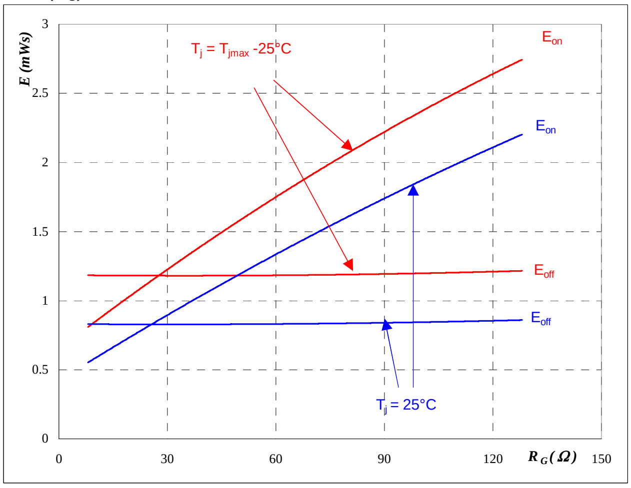
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

Figure 6 — Brake IGBT

Typical switching energy losses as a function of gate resistor

$E = f(R_G)$



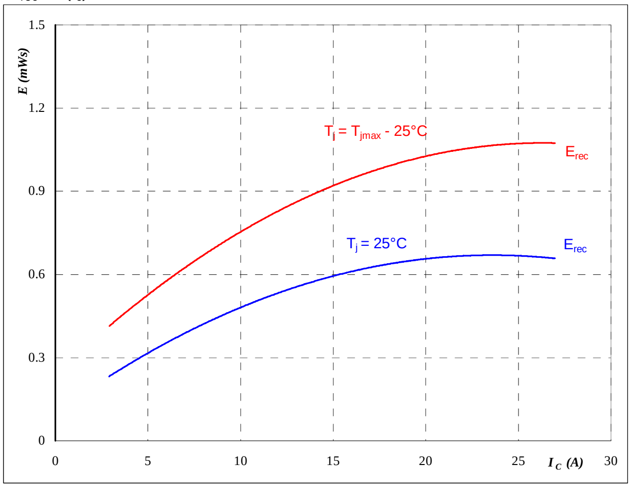
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Figure 7 — Brake IGBT

Typical reverse recovery energy loss as a function of collector current

$E_{rec} = f(I_c)$



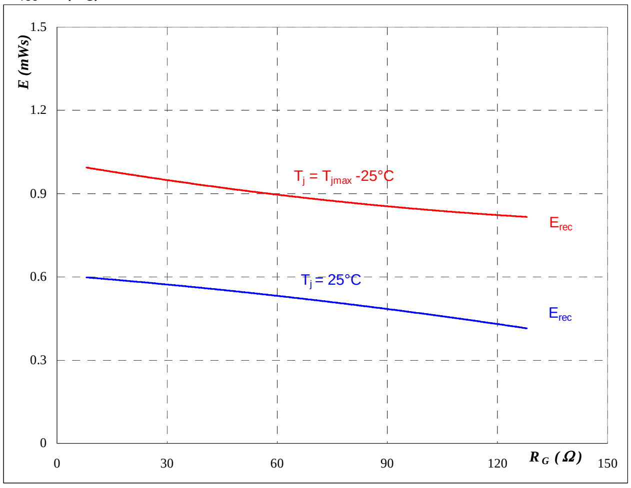
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

Figure 8 — Brake IGBT

Typical reverse recovery energy loss as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

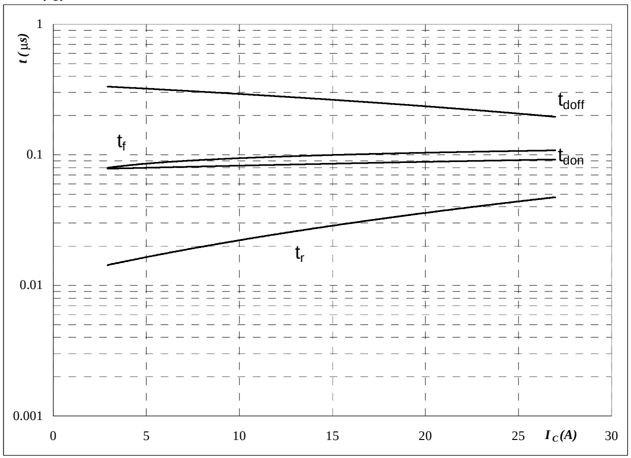
T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Brake

Figure 9 Brake IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



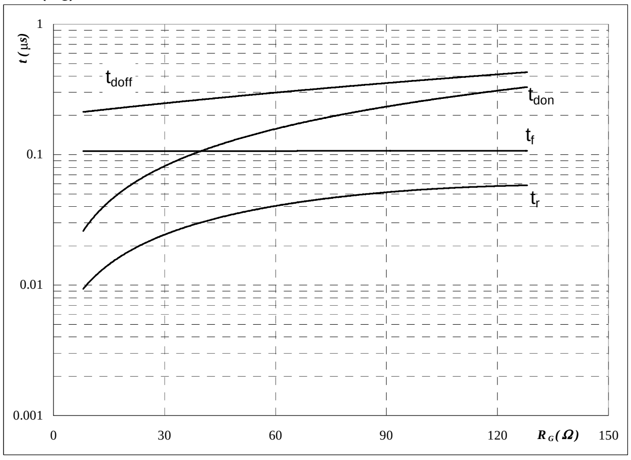
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

Figure 10 Brake IGBT

Typical switching times as a function of gate resistor

$t = f(R_G)$



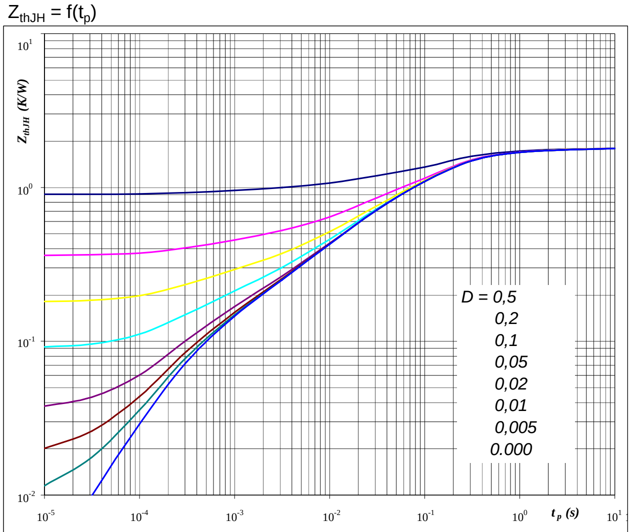
With an inductive load at

T_j =	25/125	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Figure 11 Brake IGBT

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



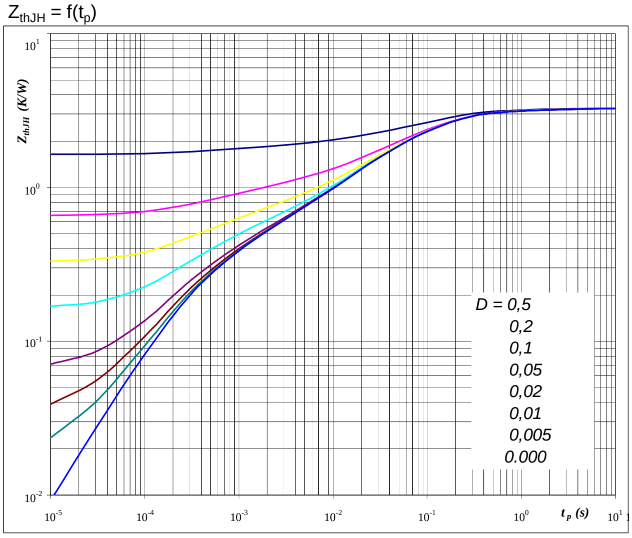
At

D =	tp / T	
R_{thJH} =	1.80	K/W

Figure 12 Brake FRED

FRED transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

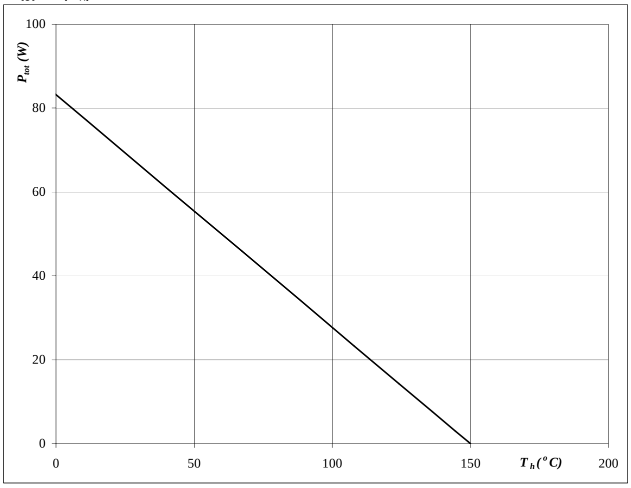
D =	tp / T	
R_{thJH} =	3.28	K/W

Brake

Figure 13 Brake IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



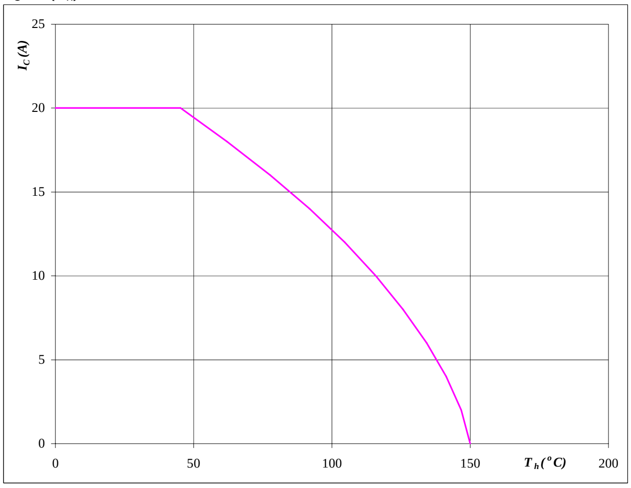
At

T_j = 150 ºC

Figure 14 Brake IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



At

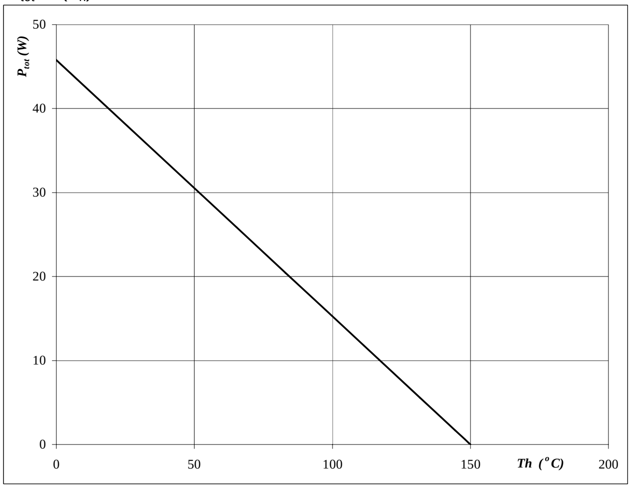
T_j = 150 ºC

V_{GE} = 15 V

Figure 15 Brake FRED

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



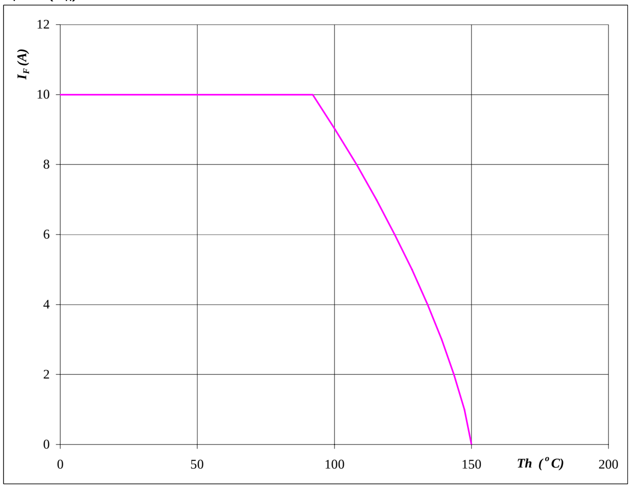
At

T_j = 150 ºC

Figure 16 Brake FRED

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

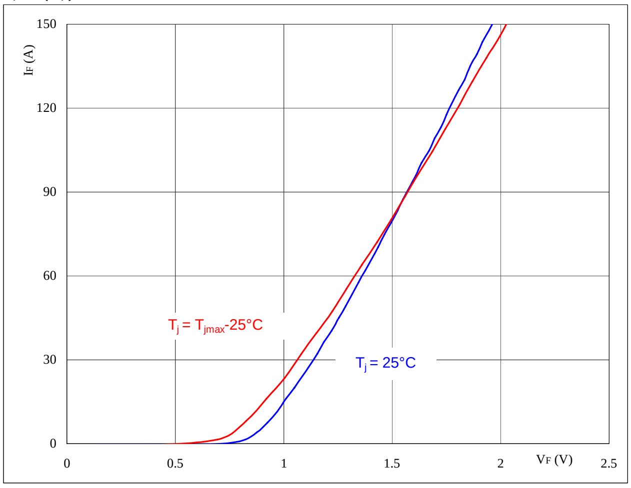
T_j = 150 ºC

Input Rectifier Bridge

Figure 1 Rectifier diode

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



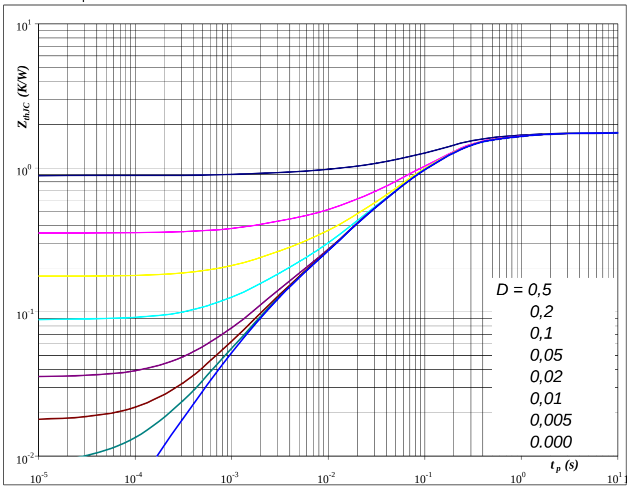
At

t_p = 250 µs

Figure 2 Rectifier diode

Diode transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

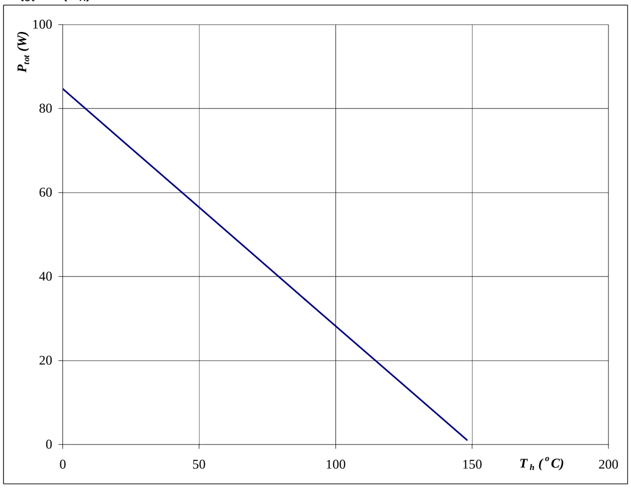
D = t_p / T

R_{thJH} = 1.770 K/W

Figure 3 Rectifier diode

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



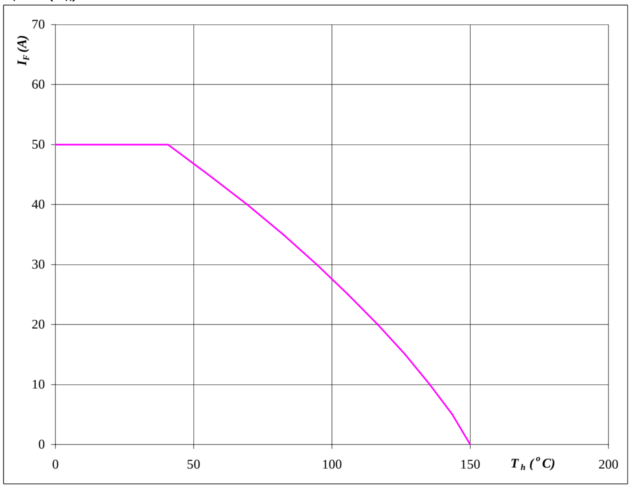
At

T_j = 150 ºC

Figure 4 Rectifier diode

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

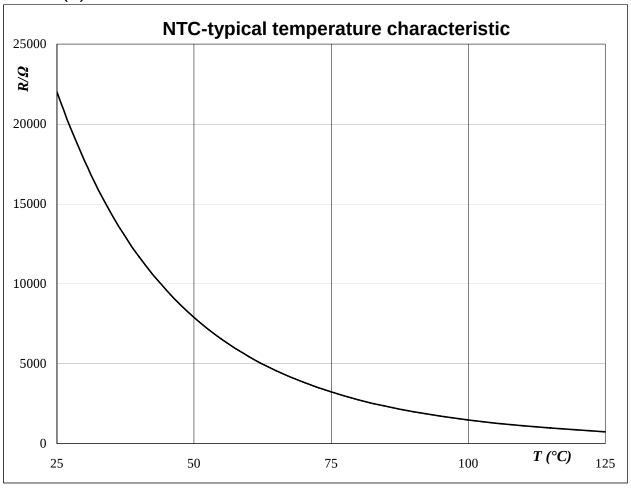
T_j = 150 ºC

Thermistor

Figure 1 Thermistor

Typical NTC characteristic
as a function of temperature

$R_T = f(T)$



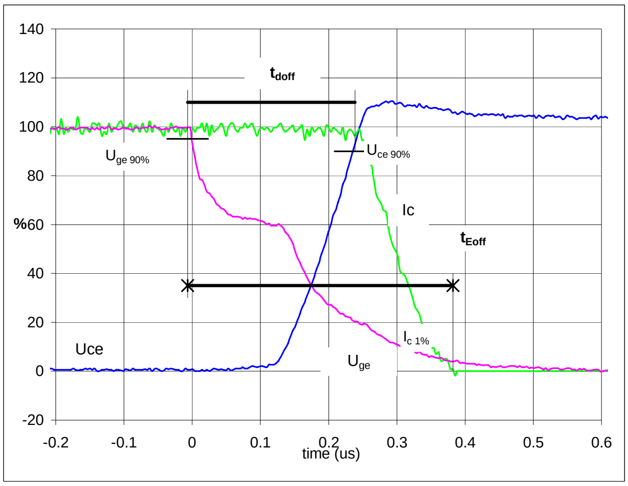
Switching Definitions Output Inverter

General conditions

T_j	=	125 °C
R_{gon}	=	16 Ω
R_{goff}	=	16 Ω

Figure 1 Output inverter IGBT

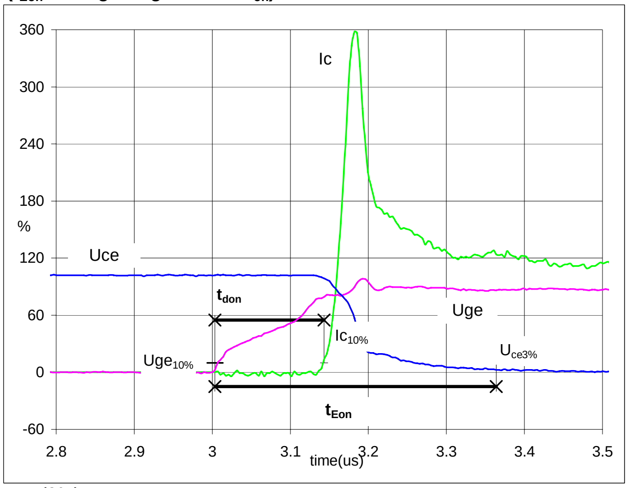
Turn-off Switching Waveforms & definition of tdoff, tEoff
(t_{Eoff} = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	25	A
t_{doff} =	0.24	µs
t_{Eoff} =	0.39	µs

Figure 2 Output inverter IGBT

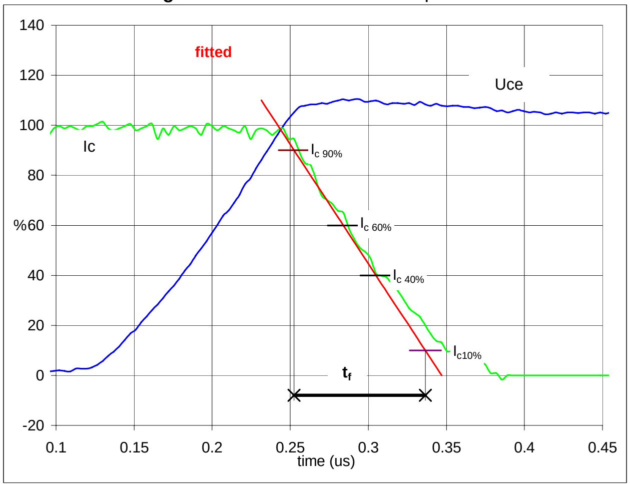
Turn-on Switching Waveforms & definition of tdon, tEon
(t_{Eon} = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	25	A
t_{don} =	0.14	µs
t_{Eon} =	0.36	µs

Figure 3 Output inverter IGBT

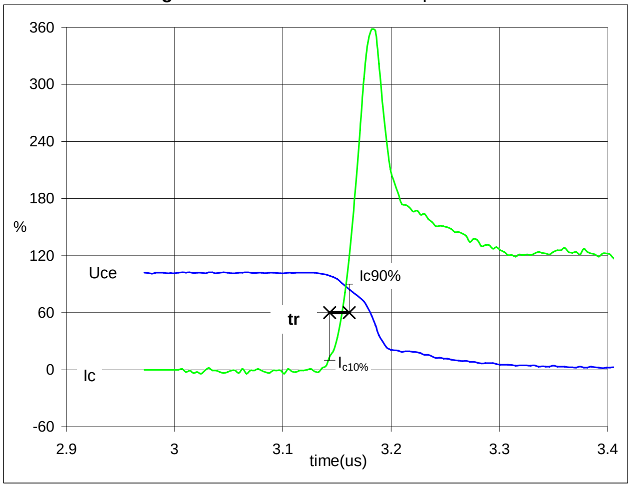
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	600	V
I_C (100%) =	25	A
t_f =	0.10	µs

Figure 4 Output inverter IGBT

Turn-on Switching Waveforms & definition of t_r

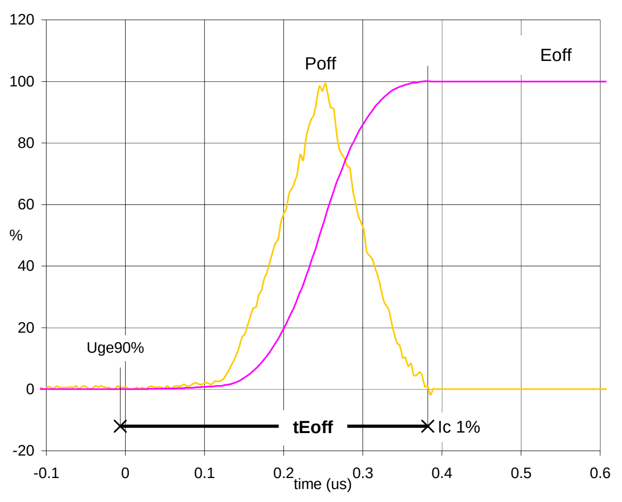


V_C (100%) =	600	V
I_C (100%) =	25	A
t_r =	0.02	µs

Switching Definitions Output Inverter

Figure 5 Output inverter IGBT

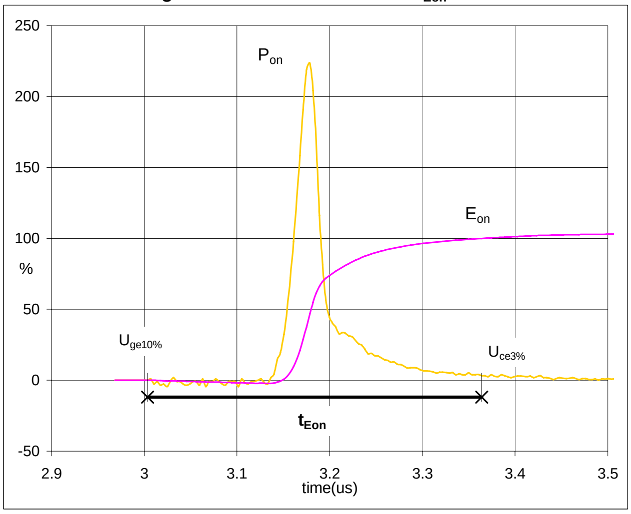
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	14.95	kW
E_{off} (100%) =	1.74	mJ
t_{Eoff} =	0.39	μs

Figure 6 Output inverter IGBT

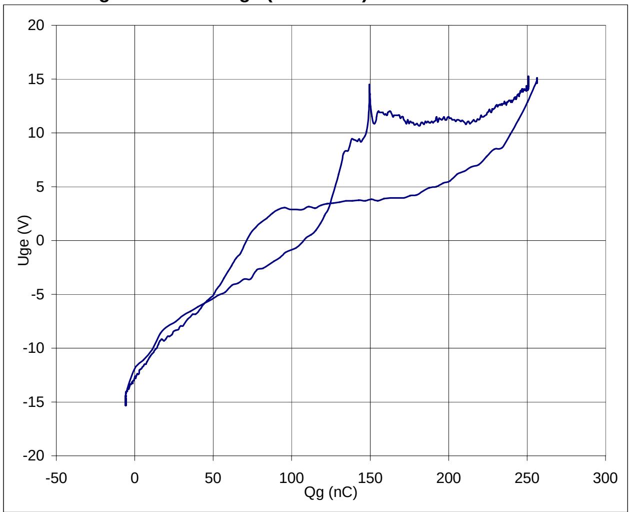
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	14.95	kW
E_{on} (100%) =	1.32	mJ
t_{Eon} =	0.36	μs

Figure 7 Output inverter FRED

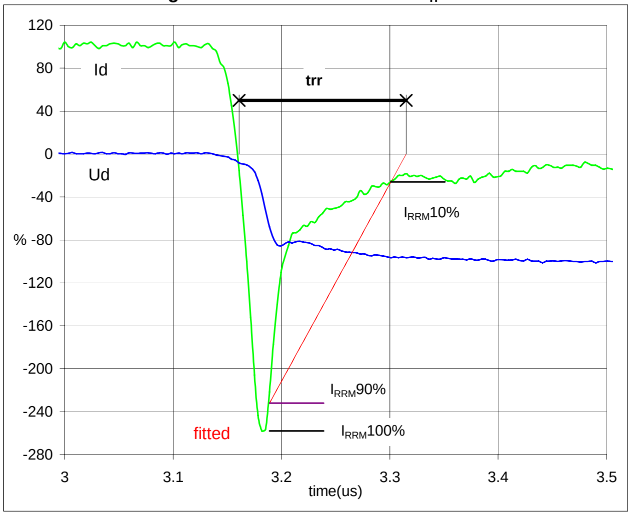
Gate voltage vs Gate charge (measured)



V_{GEoff} =	-15	V
V_{GEon} =	15	V
V_C (100%) =	600	V
I_C (100%) =	25	A
Q_g =	1175.08	nC

Figure 8 Output inverter IGBT

Turn-off Switching Waveforms & definition of t_{rr}

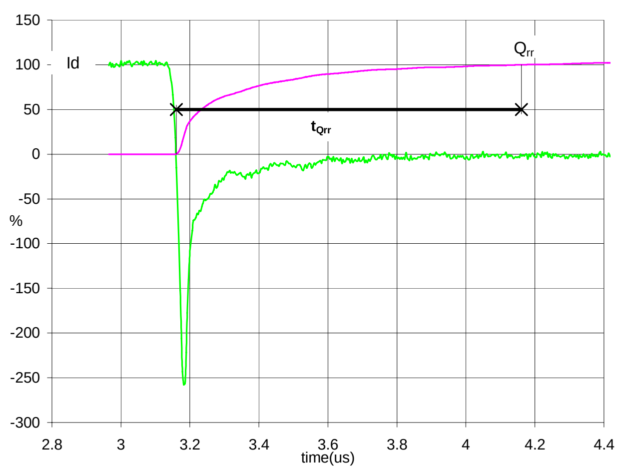


V_d (100%) =	600	V
I_d (100%) =	25	A
I_{RRM} (100%) =	-65	A
t_{rr} =	0.15	μs

Switching Definitions Output Inverter

Figure 9 Output inverter FRED

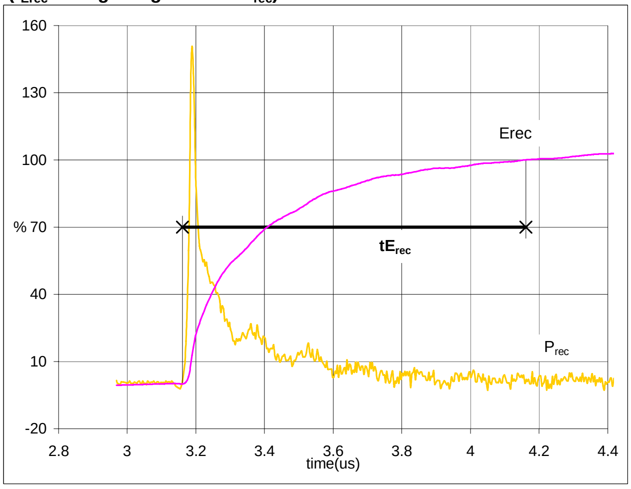
Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr} = integrating time for Q_{rr})



I_d (100%) =	25	A
Q_{rr} (100%) =	4.64	μC
t_{Qrr} =	1.00	μs

Figure 10 Output inverter FRED

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	14.95	kW
E_{rec} (100%) =	2.14	mJ
t_{Erec} =	1.00	μs

Package Outline and Pinout

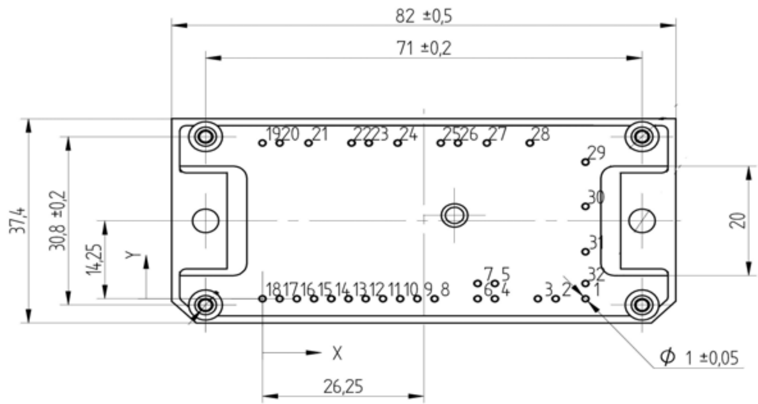
Outline

Pin table

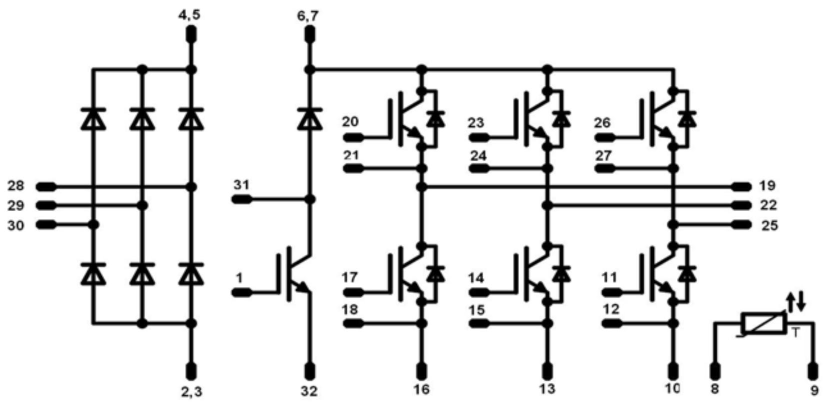
Pin	X	Y
1	52,55	0
2	47,7	0
3	44,8	0
4	37,8	0
5	37,8	2,8
6	35	0
7	35	2,8
8	28	0
9	25,2	0
10	22,4	0
11	19,6	0
12	16,8	0
13	14	0
14	11,2	0
15	8,4	0
16	5,6	0
17	2,8	0
18	0	0
19	0	28,5
20	2,8	28,5
21	7,5	28,5
22	14,5	28,5
23	17,3	28,5
24	22	28,5
25	29	28,5
26	31,8	28,5
27	36,5	28,5
28	43,5	28,5

Pin table

Pin	X	Y
29	52,55	25
30	52,55	16,9
31	52,55	8,6
32	52,55	2,8



Pinout



PRODUCT STATUS DEFINITIONS

Datasheet Status	Product Status	Definition
Target	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. The data contained is exclusively intended for technically trained staff.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data may be published at a later date. Vincotech reserves the right to make changes at any time without notice in order to improve design. The data contained is exclusively intended for technically trained staff.
Final	Full Production	This datasheet contains final specifications. Vincotech reserves the right to make changes at any time without notice in order to improve design. The data contained is exclusively intended for technically trained staff.

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.